

IN THE SPECIFICATION:

Please amend the specification as follows:

Page 5, delete paragraph [0015] and replace it with the following new paragraph:

[0015] This and other aspects are achieved according to the present invention in a lithographic apparatus an illumination system configured to form a ~~projection~~ beam of radiation from radiation provided by a radiation source, a support configured to hold a patterning device which is to be irradiated by the projection beam to pattern the ~~projection~~ beam, a substrate table configured to hold a substrate, and a projection system configured to image an irradiated portion of the patterning device onto a target portion of the substrate, wherein a reflector assembly is placed in the vicinity of the source or an image of the source, the reflector assembly including at least an inner and an outer reflector extending in the direction of an optical axis on which the source or an image of the source is located, the inner reflector being closer than the outer reflector to the optical axis, the reflectors each having an inner reflective surface and an outer backing layer, the backing layer of the inner reflector being covered with a reflective layer having a reflectivity of between 0.7 and 0.99, preferably between 0.8 and 0.99, for wavelengths between 0.1 and 100 μm , preferably between 1 and 10 μm . Thus, the reflector assembly will reflect a substantial amount of the infrared radiation that impinges upon the back of the reflector, which will reduce the heat load on the reflector assembly.